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PS3-15 Modelling the Deflection of 855 MeV Relativistic Electrons by a Bent Silicon Crystal Using TROPICS Software Package

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Modeling the deflection of 855 MeV electrons in (111) the planar channels bent crystal silicon performed by numerically solving the kinetic Fokker–Planck equation in the phase space of the transverse coordinates and velocities. It is shown that the simulation results do not describe the experiment.

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